

DOCKET NO.: 257079US8/atm

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Seikoh YOSHIDA

SERIAL NUMBER: 10/812,947

GROUP: 2822

FILED: March 31, 2004

EXAMINER: LEWIS, MONICA

FOR: NITRIDE-BASED COMPOUND SEMICONDUCTOR ELECTRON DEVICE
INCLUDING A BUFFER LAYER STRUCTURE

REQUEST TO CORRECT TITLE OF INVENTION

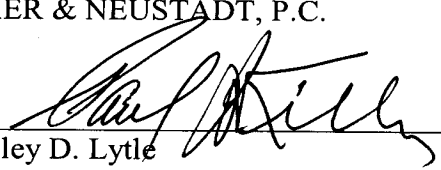
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ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: NITRIDE-BASED COMPOUND SEMICONDUCTOR ELECTRON DEVICE **INCLUDING A BUFFER LAYER STRUCTURE.**

Respectfully Submitted,

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